

1. Record Nr.	UNINA9910139568203321
Autore	Bullock Ian <1941->
Titolo	Romancing the revolution : the myth of Soviet democracy and the British left // Ian Bullock
Pubbl/distr/stampa	Athabasca University Press, 2011 Edmonton [Alta.] : , : AU Press, , 2011 ©2011
ISBN	1-926836-37-5 1-283-37030-1 9786613370303 1-926836-13-8
Descrizione fisica	1 online resource (417 pages)
Disciplina	324.24109709041
Soggetti	Socialism - Great Britain - History - 20th century Socialist parties - Great Britain - History - 20th century Soviet Union Politics and government 1917-1936 Soviet Union Foreign public opinion, British
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Introduction -- Well-prepared ground: the British left on the eve of the Russian Revolution -- Initial responses to the Russian revolution: the British left in 1917 and the Leeds "Soviet" convention -- The Bolsheviks and the British left: the October revolution and the suppression of the constituent assembly -- The myth established: the positive view of Soviet Democracy -- Polarized Social-Democrats: denunciation and debate -- Equivocal reformists: the independent Labour Party, the guild Socialists and the reaction to Kautsky -- The dictatorship of the Proletariat -- The independent Labour Party and the third international -- "An infantile disorder": Communist unity and the brief life of the Communist party (British section of the third international) -- British Bolsheviks": the Socialist Labour Party -- Pankhurst's dreadnought and the (original) fourth internationals: "Left Communism" and Soviet Democracy -- The early British Communist party: Soviet Democracy deferred and redefined -- Endings and conclusions.

Sommario/riassunto

Over two decades have passed since the collapse of the USSR, yet the words "Soviet Union" still carry significant weight in the collective memory of millions. But how often do we consider the true meaning of the term "Soviet"? Drawing extensively on left-wing press archives, *Romancing the Revolution* traces the reactions of the British Left to the idealized concept of Soviet democracy. Focusing on the turbulent period after the 1917 Russian Revolution, author Ian Bullock examines the impact of the myth of Soviet democracy: the belief that Russia was embarking on a brave experiment in a form

2. Record Nr.	UNISA996202345903316
Autore	Schroder Dieter K
Titolo	Semiconductor material and device characterization [[electronic resource] /] / Dieter K. Schroder
Pubbl/distr/stampa	[Piscataway, NJ], : IEEE Press Hoboken, N.J., : Wiley, c2006
ISBN	1-280-65470-8 9786610654703 0-470-36250-2 0-471-74909-5 0-471-74908-7
Edizione	[3rd ed.]
Descrizione fisica	1 online resource (799 p.)
Classificazione	549.8 621.3815/2
Disciplina	621.3815/2
Soggetti	Semiconductors Semiconductors - Testing
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	"Wiley-Interscience."
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Resistivity -- Carrier and doping density -- Contact resistance and Schottky barriers -- Series resistance, channel length and width, and threshold voltage -- Defects -- Oxide and interface trapped charges, oxide thickness -- Carrier lifetimes -- Mobility -- Charge-based and probe characterization -- Optical characterization -- Chemical and

physical characterization -- Reliability and failure analysis.

Sommario/riassunto

This Third Edition updates a landmark text with the latest findings. The Third Edition of the internationally lauded *Semiconductor Material and Device Characterization* brings the text fully up-to-date with the latest developments in the field and includes new pedagogical tools to assist readers. Not only does the Third Edition set forth all the latest measurement techniques, but it also examines new interpretations and new applications of existing techniques. *Semiconductor Material and Device Characterization* remains the sole text dedicated to characterization techniques for measuring semiconductor materials and devices. Coverage includes the full range of electrical and optical characterization methods, including the more specialized chemical and physical techniques. Readers familiar with the previous two editions will discover a thoroughly revised and updated Third Edition, including:

- Updated and revised figures and examples reflecting the most current data and information.
- 260 new references offering access to the latest research and discussions in specialized topics.
- New problems and review questions at the end of each chapter to test readers' understanding of the material.

In addition, readers will find fully updated and revised sections in each chapter. Plus, two new chapters have been added:

- **Charge-Based and Probe Characterization** introduces charge-based measurement and Kelvin probes. This chapter also examines probe-based measurements, including scanning capacitance, scanning Kelvin force, scanning spreading resistance, and ballistic electron emission microscopy.
- **Reliability and Failure Analysis** examines failure times and distribution functions, and discusses electromigration, hot carriers, gate oxide integrity, negative bias temperature instability, stress-induced leakage current, and electrostatic discharge.

Written by an internationally recognized authority in the field, *Semiconductor Material and Device Characterization* remains essential reading for graduate students as well as for professionals working in the field of semiconductor devices and materials. An Instructor's Manual presenting detailed solutions to all the problems in the book is available from the Wiley editorial department.
